# TS16MLD64V3D5

**184PIN DDR333 Unbuffered DIMM**
**128MB With 16Mx8 CL2.5**

## Description

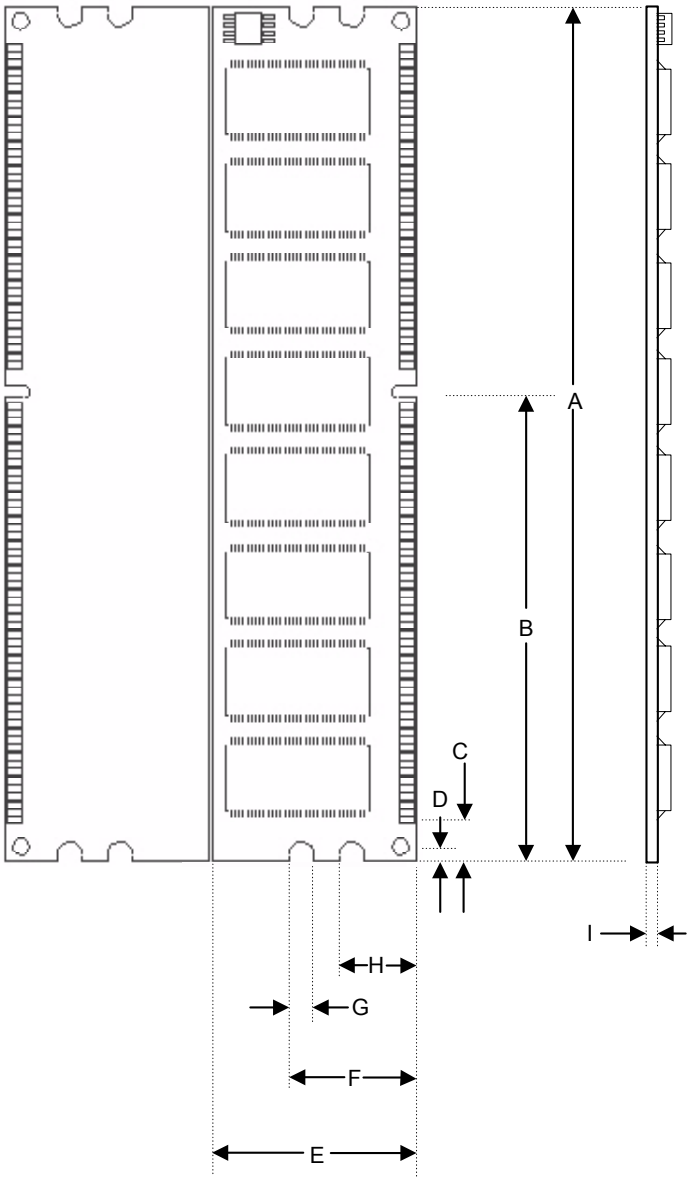
The TS16MLD64V3D5 is a 16M x 64bits Double Data Rate SDRAM high-density for DDR333. The TS16MLD64V3D5 consists of 8pcs CMOS 16Mx8 bits Double Data Rate SDRAMs in 66 pin TSOP-II 400mil packages and a 2048 bits serial EEPROM on a 184-pin printed circuit board. The TS16MLD64V3D5 is a Dual In-Line Memory Module and is intended for mounting into 184-pin edge connector sockets.

Synchronous design allows precise cycle control with the use of system clock. Data I/O transactions are possible on both edges of DQS. Range of operation frequencies, programmable latencies allow the same device to be useful for a variety of high bandwidth, high performance memory system applications.

## Features

- Power supply: VDD: 2.5V ± 0.2V, VDDQ: 2.5V ± 0.2V
- Max clock Freq: 166MHZ.
- Double-data-rate architecture; two data transfers per clock cycle
- Differential clock inputs (CK and /CK)
- DLL aligns DQ and DQS transition with CK transition
- Auto and Self Refresh 15.6us refresh interval.
- Data I/O transactions on both edge of data strobe.
- Edge aligned data output, center aligned data input.
- Serial Presence Detect (SPD) with serial EEPROM
- SSTL-2 compatible inputs and outputs.
- MRS cycle with address key programs.
  - CAS Latency (Access from column address): 2.5
  - Burst Length (2,4,8)
  - Data Sequence (Sequential & Interleave)

## Placement




**PCB: 09-1395**

## Dimensions

| Side | Millimeters | Inches |
|---|---|---|
| A | 133.35±0.20 | 5.250±0.008 |
| B | 72.39 | 2.850 |
| C | 6.35 | 0.250 |
| D | 2.20 | 0.087 |
| E | 31.75±0.20 | 1.250±0.008 |
| F | 19.80 | 0.779 |
| G | 4.00 | 0.157 |
| H | 12.00 | 0.472 |
| I | 1.27±0.10 | 0.050±0.004 |

**(Refer Placement)**

## Pin Identification

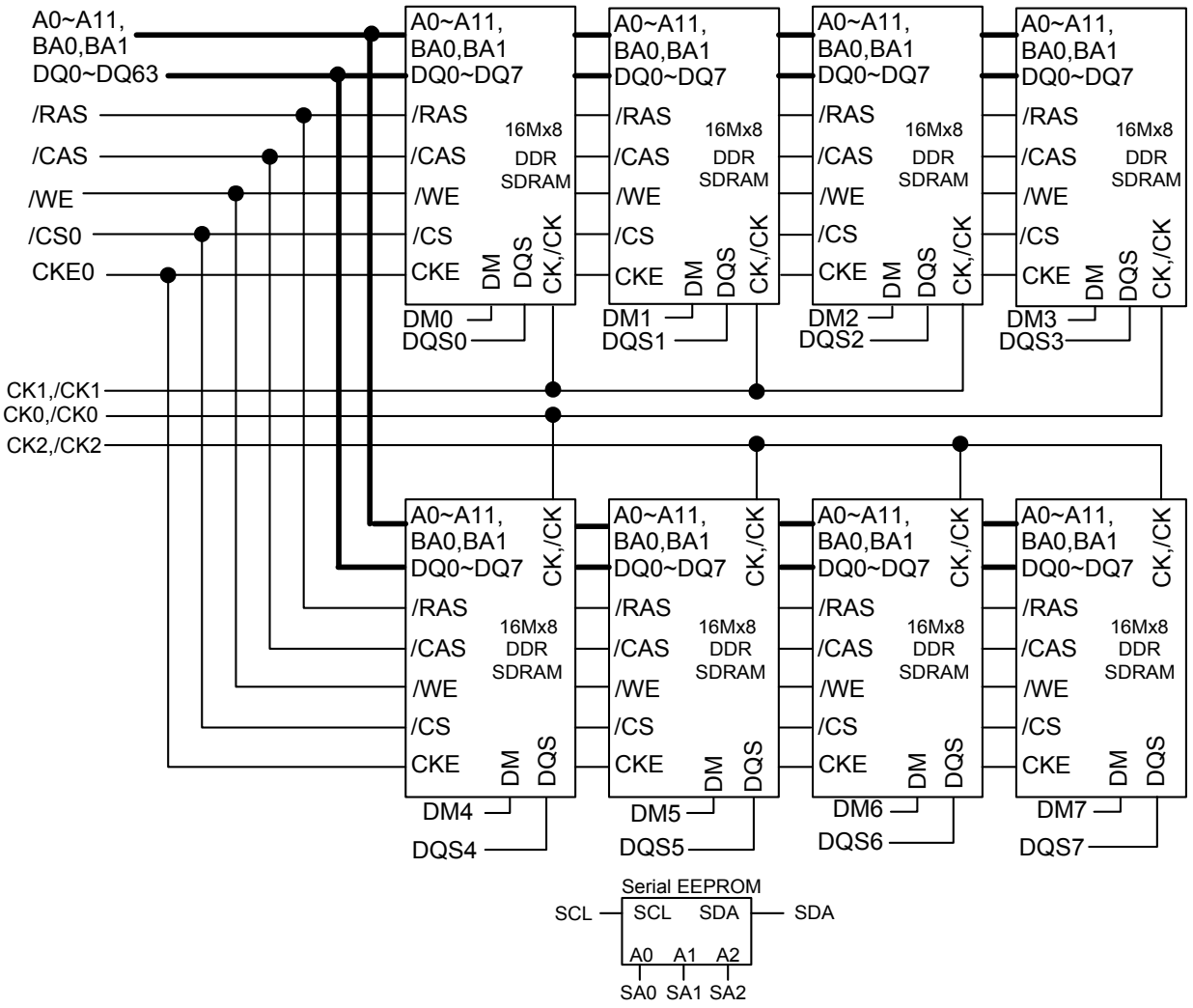
| Symbol | Function |
|---|---|
| A0~A11,BA0,BA1 | Address input |
| DQ0~DQ63 | Data Input / Output. |
| DQS0~DQS7 | Data strobe input/output |
| CK0, /CK0, CK1, /CK1 CK2, /CK2 | Clock Input. |
| CKE0 | Clock Enable Input. |
| /CS0 | Chip Select Input. |
| /RAS | Row Address Strobe |
| /CAS | Column Address Strobe |
| /WE | Write Enable |
| DM0~DM7 | Data-in Mask |
| VDD | +2.5 Voltage power supply |
| VDDQ | +2.5 Voltage Power Supply for DQS |
| VREF | Power Supply for Reference |
| VDDSPD | +2.5 Voltage Serial EEPROM Power Supply |
| SA0~SA2 | Address in EEPROM |
| SCL | Serial PD Clock |
| SDA | Serial PD Add/Data input/output |
| VSS | Ground |
| NC | No Connection |

**Pinouts:**

| Pin No | Pin Name | Pin No | Pin Name | Pin No | Pin Name | Pin No | Pin Name |
|---|---|---|---|---|---|---|---|
| 01 | VREF | 47 | *DQS8 | 93 | VSS | 139 | VSS |
| 02 | DQ0 | 48 | A0 | 94 | DQ4 | 140 | *DM8 |
| 03 | VSS | 49 | *CB2 | 95 | DQ5 | 141 | A10 |
| 04 | DQ1 | 50 | VSS | 96 | VDDQ | 142 | *CB6 |
| 05 | DQS0 | 51 | *CB3 | 97 | DM0 | 143 | VDDQ |
| 06 | DQ2 | 52 | BA1 | 98 | DQ6 | 144 | *CB7 |
| 07 | VDD | 53 | DQ32 | 99 | DQ7 | 145 | VSS |
| 08 | DQ3 | 54 | VDDQ | 100 | VSS | 146 | DQ36 |
| 09 | NC | 55 | DQ33 | 101 | NC | 147 | DQ37 |
| 10 | NC | 56 | DQS4 | 102 | NC | 148 | VDD |
| 11 | VSS | 57 | DQ34 | 103 | NC | 149 | DM4 |
| 12 | DQ8 | 58 | VSS | 104 | VDDQ | 150 | DQ38 |
| 13 | DQ9 | 59 | BA0 | 105 | DQ12 | 151 | DQ39 |
| 14 | DQS1 | 60 | DQ35 | 106 | DQ13 | 152 | VSS |
| 15 | VDDQ | 61 | DQ40 | 107 | DM1 | 153 | DQ44 |
| 16 | *CK1 | 62 | VDDQ | 108 | VDD | 154 | /RAS |
| 17 | */CK1 | 63 | /WE | 109 | DQ14 | 155 | DQ45 |
| 18 | VSS | 64 | DQ41 | 110 | DQ15 | 156 | VDDQ |
| 19 | DQ10 | 65 | /CAS | 111 | *CKE1 | 157 | /CS0 |
| 20 | DQ11 | 66 | VSS | 112 | VDDQ | 158 | */CS1 |
| 21 | CKE0 | 67 | DQS5 | 113 | NC | 159 | DM5 |
| 22 | VDDQ | 68 | DQ42 | 114 | DQ20 | 160 | VSS |
| 23 | DQ16 | 69 | DQ43 | 115 | *A12 | 161 | DQ46 |
| 24 | DQ17 | 70 | VDD | 116 | VSS | 162 | DQ47 |
| 25 | DQS2 | 71 | NC | 117 | DQ21 | 163 | NC |
| 26 | VSS | 72 | DQ48 | 118 | A11 | 164 | VDDQ |
| 27 | A9 | 73 | DQ49 | 119 | DM2 | 165 | DQ52 |
| 28 | DQ18 | 74 | VSS | 120 | VDD | 166 | DQ53 |
| 29 | A7 | 75 | */CK2 | 121 | DQ22 | 167 | NC |
| 30 | VDDQ | 76 | *CK2 | 122 | A8 | 168 | VDD |
| 31 | DQ19 | 77 | VDDQ | 123 | DQ23 | 169 | DM6 |
| 32 | A5 | 78 | DQS6 | 124 | VSS | 170 | DQ54 |
| 33 | DQ24 | 79 | DQ50 | 125 | A6 | 171 | DQ55 |
| 34 | VSS | 80 | DQ51 | 126 | DQ28 | 172 | VDDQ |
| 35 | DQ25 | 81 | VSS | 127 | DQ29 | 173 | NC |
| 36 | DQS3 | 82 | NC | 128 | VDDQ | 174 | DQ60 |
| 37 | A4 | 83 | DQ56 | 129 | DM3 | 175 | DQ61 |
| 38 | VDD | 84 | DQ57 | 130 | A3 | 176 | VSS |
| 39 | DQ26 | 85 | VDD | 131 | DQ30 | 177 | DM7 |
| 40 | DQ27 | 86 | DQS7 | 132 | VSS | 178 | DQ62 |
| 41 | A2 | 87 | DQ58 | 133 | DQ31 | 179 | DQ63 |
| 42 | VSS | 88 | DQ59 | 134 | *CB4 | 180 | VDDQ |
| 43 | A1 | 89 | VSS | 135 | *CB5 | 181 | SA0 |
| 44 | *CB0 | 90 | NC | 136 | VDDQ | 182 | SA1 |
| 45 | *CB1 | 91 | SDA | 137 | CK0 | 183 | SA2 |
| 46 | VDD | 92 | SCL | 138 | /CK0 | 184 | VDDSPD |

* Please refer Block Diagram

## Block Diagram





This technical information is based on industry standard data and tests believed to be reliable. However, Transcend makes no warranties, either expressed or implied, as to its accuracy and assume no liability in connection with the use of this product. Transcend reserves the right to make changes in specifications at any time without prior notice.

## ABSOLUTE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Voltage on any pin relative to Vss | VIN, VOUT | -0.5 ~ 3.6 | V |
| Voltage on $V_{DD}$ supply to Vss | VDD, VDDQ | -1.0 ~ 3.6 | V |
| Storage temperature | $T_{STG}$ | -55~+150 | °C |
| Power dissipation | $P_D$ | 12 | W |
| Short circuit current | $I_{OS}$ | 50 | mA |
| Mean time between failure | MTBF | 50 | year |
| Temperature Humidity Burning | THB | 85°C/85%, Static Stress | °C-% |
| Temperature Cycling Test | TC | 0°C ~ 125°C Cycling | °C |

**Note:** Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded.
Functional operation should be restricted to recommended operating condition.
Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

## DC OPERATING CONDITIONS

**Recommended operating conditions (Voltage referenced to Vss = 0V, $T_A$ = 0 to 70°C)**

| Parameter | Symbol | Min | Max | Unit | Note |
|---|---|---|---|---|---|
| Supply voltage | VDD | 2.3 | 2.7 | V | |
| I/O Supply voltage | VDDQ | 2.3 | 2.7 | V | |
| I/O Reference voltage | VREF | $V_{DDQ}$/2-50mV | $V_{DDQ}$/2+50mV | V | 1 |
| I/O Termination voltage | VTT | $V_{REF}$-0.04 | $V_{REF}$+0.04 | V | 2 |
| Input logic high voltage | VIH(DC) | $V_{REF}$+0.15 | $V_{DDQ}$+0.3 | V | 4 |
| Input logic low voltage | VIL(DC) | -0.3 | $V_{REF}$-0.15 | V | 4 |
| Input Voltage Level, CK and /CK inputs | VIN(DC) | -0.3 | $V_{DDQ}$+0.3 | V | |
| Input Differential Voltage, CK and /CK inputs | VID(DC) | 0.3 | $V_{DDQ}$+0.6 | V | 3 |
| Input crossing point voltage, CK and /CK inputs | VIX(DC) | 1.15 | 1.35 | V | 5 |
| Input leakage current | $I_I$ | -2 | 2 | uA | |
| Output leakage current | $I_{OZ}$ | -5 | 5 | uA | |
| Output High Current (Normal strength driver) VOUT= VTT + 0.84V | $I_{OH}$ | -16.8 | | mA | |
| Output Low Current (Normal strength driver) VOUT= VTT – 0.84V | $I_{OL}$ | 16.8 | | mA | |
| Output High Current (Half strength driver) VOUT= VTT + 0.45V | $I_{OH}$ | -9 | | mA | |
| Output High Current (Half strength driver) VOUT= VTT - 0.45V | $I_{OL}$ | 9 | | mA | |

**Note:**
1. Includes ± 25mV margin for DC offset on VREF, and a combined total of ± 50mV margin for all AC noise and DC offset on VREF, bandwidth limited to 20MHz. The DRAM must accommodate DRAM current spikes on VREF and internal DRAM noise coupled. TO VREF, both of which may result in VREF noise. VREF should be de-coupled with an inductance of <=3nH.
2. $V_{TT}$ is not applied directly to the device. $V_{TT}$ is a system supply for signal termination resistors, is expected to be set equal to VREF, and must track variations in the DC level of VREF
3. $V_{ID}$ is the magnitude of the difference between the input level on CK and the input level on /CK.
4. These parameters should be tested at the pin on actual components and may be checked at either the pin or the pad in simulation. The AC and DC input specifications are relative to a VREF envelop that has been bandwidth limited to 200MHZ.
5. The value of $V_{IX}$ is expected to equal 0.5*VDDQ of the transmitting device and must track variations in the dc level of the same.

## DC CHARACTERISTICS

**(Recommended operating condition unless otherwise noted, VDD=2.7V, TA = 10 °C)**

| Parameter | Symbol | Max. | Unit | Note |
|---|---|---|---|---|
| Operating current - One bank Active-Precharge; tRC=tRCmin; tCK=166MHZ for DDR333 DQ, DM and DQS inputs changing twice per clock cycle; Address and control inputs changing once per clock cycle | IDD0 | 840 | mA | |
| Operating current - One bank operation; One bank open, Burst=4; Reads - Refer to the following page for detailed test condition. | IDD1 | 1040 | mA | |
| Percharge power-down standby current; All banks idle; power –down mode; CKE = <VIL(max); tCK=166MHZ for DDR333, VIN = VREF for DQ,DQS and DM | IDD2P | 28 | mA | |
| Precharge Floating standby current; CS# > =VIH(min);All banks idle; CKE > = VIH(min); tCK=166MHZ for DDR333, Address and other control inputs changing once per clock cycle; VIN = VREF for DQ,DQS and DM | IDD2F | 200 | mA | |
| Precharge Quiet Standby current; CS#>=VIH (min); All banks idle; CKE>=VIH(min); tCK=166MHZ for DDR333; Address and other control inputs stable with keeping >=VIH(min) or =< VIL(max); VIN=VREF for DQ,DQS and DM | IDD2Q | 144 | ma | |
| Active power - down standby current ; one bank active; power-down mode; CKE<= VIL (max); tCK=166MHZ for DDR333; VIN = VREF for DQ,DQS and DM | IDD3P | 280 | mA | |
| Active standby current; CS# >= VIH(min); CKE>=VIH(min); one bank active; active - precharge; tRC=tRASmax; tCK=166MHZ for DDR333; DQ, DQS and DM inputs changing twice per clock cycle; Address and other control inputs changing once per clock cycle | IDD3N | 480 | mA | |
| Operating current - burst read; Burst length = 2; reads; continuous burst; One bank active; address and control inputs changing once per clock cycle; 50% of data changing at every burst; Iout = 0 mA | IDD4R | 1280 | mA | |
| Operating current - burst write; Burst length = 2; writes; continuous burst; One bank active address and control inputs changing once per clock cycle; CL=2.5 at tCK=166MHZ for DDR333; DQ, DM and DQS inputs changing twice per clock cycle, 50% of input data changing at every burst | IDD4W | 1216 | mA | |
| Auto refresh current; tRC = tRFC(min), 10*tCK for DDR333at 166Mhz; distributed refresh | IDD5 | 1520 | mA | |
| Self refresh current; CKE <= 0.2V; External clock should be on; tCK=166MHZ for DDR333; | IDD6 | 16 | mA | |
| Operating current - Four bank operation; Four bank interleaving with BL=4 -Refer to the following page for detailed test condition | IDD7 | 2640 | mA | |

**Note:** 1. Module IDD was calculated on the basis of component IDD and can be differently measured according to DQ loading capacitor.

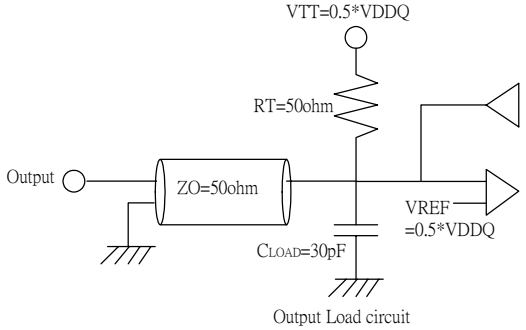
## AC OPERATING CONDITIONS

| Parameter | Symbol | Min | Max | Unit | Note |
|---|---|---|---|---|---|
| Input High (Logic 1) Voltage, DQ, DQS and DM signals | VIH(AC) | VREF + 0.31 | | V | 3 |
| Input Low (Logic 0) Voltage, DQ, DQS and DM signals | VIL(AC) | | VREF - 0.31 | V | 3 |
| Input Differential Voltage, CK and /CK inputs | VID(AC) | 0.7 | VDDQ + 0.6 | V | 1 |
| Input Crossing Point Voltage, CK and /CK inputs | VIX(AC) | 0.5*VDDQ - 0.2 | 0.5*VDDQ + 0.2 | V | 2 |

**Note:**
1. VID is the magnitude of the difference between the input level on CK and the input on /CK.
2. The value of VIX is expected to equal 0.5*V DDQ of the transmitting device and must track variations in the DC level of the same.
3. These parameters should be tested at the pin on actual components and may be checked at either the pin or the pad in simulation. The AC and DC input specifications are relative to a VREF envelope that has been bandwidth limited 20MHz.

## AC OPERATING TEST CONDITIONS (VDD=2.5, VDDQ=2.5, TA=0 to 70°C)

| Parameter | Value | Unit | Note |
|---|---|---|---|
| Input reference voltage for Clock | 0.5*VDDQ | V | |
| Input signal maximum peak swing | 1.5 | V | |
| Input Levels(VIH/VIL) | VREF+0.31/VREF-0.31 | V | |
| Input timing measurement reference level | VREF | V | |
| Output timing measurement reference level | VTT | V | |
| Output load condition | See Load Circuit | | |



Output Load circuit

## Input/Output CAPACITANCE (VDD = 2.5V, VDDQ = 2.5V,TA = 25°C, f = 1MHz)

| Parameter | Symbol | Min | Max | Unit |
|---|---|---|---|---|
| Input capacitance (A0~A11, BA0~BA1, /RAS, /CAS, /WE) | CIN1 | 49 | 57 | pF |
| Input capacitance (CKE0) | CIN2 | 42 | 50 | pF |
| Input capacitance (/CS0) | CIN3 | 42 | 50 | pF |
| Input capacitance (CK0 ~ CK2) | CIN4 | 22 | 25 | pF |
| Input capacitance (DM0~DM7) | CIN5 | 6 | 8 | pF |
| Data and DQS input/output capacitance (DQ0~DQ63) | COUT | 6 | 8 | pF |

## AC Timing Parameters & Specifications

**(These AC characteristics were tested on the Component)**

| Parameter | Symbol | Min | Max | Unit | Note |
|---|---|---|---|---|---|
| Row cycle time | tRC | 60 | | ns | |
| Refresh row cycle time | tRFC | 72 | | ns | |
| Row active time | tRAS | 42 | 120K | ns | |
| /RAS to /CAS delay | tRCD | 18 | | ns | |
| Row active to Row active delay | tRP | 18 | | ns | |
| Row active to Row active delay | tRRD | 12 | | ns | |
| Write recovery time | tWR | 15 | | ns | |
| Last data in to Read command | tWTR | 1 | | tCK | |
| Col. Address to Col. Address delay | tCCD | 1 | | tCK | |
| Clock cycle time | tCK | 6 | | ns | |
| Clock high level width | tCH | 0.45 | 0.55 | tCK | |
| Clock low level width | tCL | 0.45 | 0.55 | tCK | |
| DQS-out access time from CK /CK | tDQSCK | -0.6 | 0.6 | ns | |
| Output data access time from CK /CK | tAC | -0.7 | 0.7 | ns | |
| Data strobe edge to output data edge | tDQSQ | | 0.45 | ns | |
| Read Preamble | tRPRE | 0.9 | 1.1 | tCK | |
| Read Postamble | tRPST | 0.4 | 0.6 | tCK | |
| CK to valid DQS-in | tDQSS | 0.75 | 1.25 | tCK | |
| DQS-in setup time | tWPRES | 0 | | ns | 2 |
| DQS-in hold time | tWPREH | 0.25 | | tCK | |
| DQS falling edge to CK rising-setup time | tDSS | 0.2 | | tCK | |
| DQS falling edge from CK rising-hold time | tDSH | 0.2 | | tCK | |
| DQS-in high level width | tDQSH | 0.35 | | tCK | |
| DQS-in low level width | tDQSL | 0.35 | | tCK | |
| DQS-in cycle time | tDSC | 0.9 | 1.1 | tCK | |
| Address and Control input setup time | tIS | 0.8 | | ns | |
| Address and Control input hold time | tIH | 0.8 | | ns | |
| Data-out high-impedance time from CK, /CK | tHZ | tACmin-400ps | tACman-400ps | ns | |
| Data-out low-impedance time from CK, /CK | tLZ | tACmin-400ps | tACman-400ps | ns | |
| Mode register set cycle time | tMRD | 12 | | ns | |
| DQ & DM setup time to DQS | tDS | 0.45 | | ns | |
| DQ & DM hold time to DQS | tDH | 0.45 | | ns | |
| DQ & DM input pulse width | tDIPW | 1.75 | | ns | |
| Power down exit time | tPDEX | 6 | | ns | |
| Exit self refresh to write command | tXSW | | | ns | |
| Exit self refresh to bank active command | tXSA | 75 | | | |
| Exit self refresh to read command | tXSR | 200 | | tCK | |
| Refresh interval time | tREF | 15.6 | | us | 1 |
| Clock half period | tHP | TCLmin or tCHmin | | ns | |
| Data hold skew factor | tQHS | | 0.75 | ns | |
| DQS write postamble time | tWPST | 0.4 | | tCK | 3 |

Note:
1. Maximum burst refresh of 8
2. The specific requirement is that DQS be valid (High or Low) on or before this CK edge. The case shown (DQS going from High_Z to logic Low) applies when no writes were previously in progress on the bus. If a previous write was in progress, DQS could be High at this time, depending on tDQSS.
3. The Maximum limit for this parameter is not a device limit. The device will operate with a great value for this parameter, but system performance (bus turnaround) will degrade accordingly.

## SIMPLIFIED TRUTH TABLE

(V=Valid, X=Don't Care, H=Logic High, L=Logic Low)

| COMMAND | | | CKEn-1 | CKEn | /CS | /RAS | /CAS | /WE | $BA_{0,1}$ | $A_{10}$/AP | $A_0$~$A_9$, $A_{11}$ | Note |
|---|---|---|---|---|---|---|---|---|---|---|---|---|
| Register | Extended Mode Register Set | | H | X | L | L | L | L | OP CODE | | | 1,2 |
| Register | Mode Register Set | | H | X | L | L | L | L | OP CODE | | | 1,2 |
| Refresh | Auto Refresh | | H | H | L | L | L | H | X | | | 3 |
| | Self Refresh | Entry | | L | | | | | | | | 3 |
| | | Exit | L | H | L | H | H | H | X | | | 3 |
| | | | | | H | X | X | X | | | | 3 |
| Bank Active & Row Addr. | | | H | X | L | L | H | H | V | Row Address | | |
| Read & Column Address | Auto Precharge Disable | | H | X | L | H | L | H | V | L | Column Address ($A_0$~$A_9$) | 4 |
| | Auto Precharge Enable | | | | | | | | | H | | 4 |
| Write & Column Address | Auto Precharge Disable | | H | X | L | H | L | L | V | L | Column Address ($A_0$~$A_9$) | 4 |
| | Auto Precharge Enable | | | | | | | | | H | | 4, 6 |
| Burst Stop | | | H | X | L | H | H | L | X | | | 7 |
| Precharge | Bank Selection | | H | X | L | L | H | L | V | L | X | |
| | All Banks | | | | | | | | X | H | | 5 |
| Active Power Down | Entry | | H | L | H | X | X | X | X | | | |
| | | | | | L | V | V | V | | | | |
| | Exit | | L | H | X | X | X | X | | | | |
| Precharge Power Down Mode | Entry | | H | L | H | X | X | X | X | | | |
| | | | | | L | H | H | H | | | | |
| | Exit | | L | H | H | X | X | X | | | | |
| | | | | | L | V | V | V | | | | |
| DM | | | H | X | | | | | X | | | 8 |
| No Operation Command | | | H | X | H | X | X | X | X | | | 9 |
| | | | | | L | H | H | H | | | | 9 |

Note:
1. OP Code: Operand Code. A0 ~ A11 & BA0 ~ BA1: Program keys. (@EMRS/MRS)
2. EMRS/ MRS can be issued only at all banks precharge state. A new command can be issued 2 clock cycles after EMRS or MRS.
3. Auto refresh functions are same as the CBR refresh of DRAM. The automatic precharge without row precharge command is meant by "Auto". Auto/self refresh can be issued only at all banks precharge state.
4. BA0 ~ BA1: Bank select addresses. If both BA0 and BA1 are "Low" at read, write, row active and precharge, bank A is selected. If both BA0 is "High" and BA1 is "Low" at read, write, row active and precharge, bank B is selected. If both BA0 is "Low" and BA1 is "High" at read, write, row active and precharge, bank C is selected. If both BA0 and BA1 are "High" at read, write, row active and precharge, bank D is selected.
5. If A10/AP is "High" at row precharge, BA0 and BA1 are ignored and all banks are selected.
6. During burst write with auto precharge, new read/write command cannot be issued. Another bank read/write command can be issued after the end of burst. New row active of the associated bank can be issued at tRP after the end of burst.
7. Burst stop command is valid at every burst length.
8. DM sampled at the rising and falling edges of the DQS and Data-in is masked at the both edges (Write DM latency is 0).
9. This combination is not defined for any function, which means "No Operation (NOP)" in DDR SDRAM.

## Serial Presence Detect Specification

| Serial Presence Detect | | | |
|---|---|---|---|
| Byte No. | Function Described | Standard Specification | Vendor Part |
| 0 | # of Bytes Written into Serial Memory | 128bytes | 80 |
| 1 | Total # of Bytes of S.P.D Memory | 256bytes | 08 |
| 2 | Fundamental Memory Type | DDR SDRAM | 07 |
| 3 | # of Row Addresses on this Assembly | 12 | 0C |
| 4 | # of Column Addresses on this Assembly | 10 | 0A |
| 5 | # of Module Rows on this Assembly | 1 bank | 01 |
| 6 | Data Width of this Assembly | 64bits | 40 |
| 7 | Data Width of this Assembly | - | 00 |
| 8 | VDDQ and Interface Standard of this Assembly | SSTL 2.5V | 04 |
| 9 | DDR SDRAM Cycle Time at CAS Latency=2.5 | 6ns | 60 |
| 10 | DDR SDRAM Access Time from Clock at CL=2.5 | ±0.7ns | 70 |
| 11 | DIMM configuration type (non-parity, Parity, ECC) | NON-ECC | 00 |
| 12 | Refresh Rate Type | 15.625us/Self Refresh | 80 |
| 13 | Primary DDR SDRAM Width | X8 | 08 |
| 14 | Error Checking DDR SDRAM Width | - | 00 |
| 15 | Min Clock Delay for Back to Back Random Column Address | tCCD=1CLK | 01 |
| 16 | Burst Lengths Supported | 2,4,8 | 0E |
| 17 | # of banks on each DDR SDRAM device | 4 bank | 04 |
| 18 | CAS Latency supported | 2, 2.5 | 0C |
| 19 | CS Latency | 0 CLK | 01 |
| 20 | WE Latency | 1 CLK | 02 |
| 21 | DDR SDRAM Module Attributes | Registered address & control inputs and on-card DLL | 20 |
| 22 | DDR SDRAM Device Attributes : General | +/-0.2V voltage tolerance | 00 |
| 23 | DDR SDRAM Cycle Time CL=2.0 | 7.5ns | 75 |
| 24 | DDR SDRAM Access from Clock CL=2.0 | ±0.7ns | 70 |
| 25 | DDR SDRAM Cycle Time CL=1.5 | - | 00 |
| 26 | DDR SDRAM Access from Clock CL=1.5 | - | 00 |
| 27 | Minimum Row Precharge Time (tRP) | 18ns | 48 |
| 28 | Minimum Row Active to Row Activate delay (tRRD) | 12ns | 30 |
| 29 | Minimum RAS to CAS Delay (tRCD) | 18ns | 48 |
| 30 | Minimum active to Precharge time (tRAS) | 42ns | 2A |
| 31 | Module ROW density | 128MB | 20 |
| 32 | Command/Address Input Setup Time | 0.8ns | 80 |

| | | | | | | | | |
|---|---|---|---|---|---|---|---|---|
| 33 | Command/Address Input Hold Time | 0.8ns | 80 | | | | | |
| 34 | Data Signal Input Setup Time | 0.45ns | 45 | | | | | |
| 35 | Data Signal Input Hold Time | 0.45ns | 45 | | | | | |
| 36-61 | Superset Information | - | 00 | | | | | |
| 62 | SPD Data Revision Code | - | 00 | | | | | |
| 63 | Checksum for Bytes 0-62 | - | FD | | | | | |
| 64-71 | Manufacturers JEDEC ID | Transcend | 7F, 4F | | | | | |
| 72 | Manufacturing Location | T | 54 | | | | | |
| 73-90 | Manufacturers Part Number | TS16MLD64V3D5 | 54 | 53 | 31 | 36 | 4D | 4C |
| | | | 44 | 36 | 34 | 56 | 33 | 44 |
| | | | 35 | 20 | 20 | 20 | 20 | 20 |
| 91-92 | Revision Code | - | - | | | | | |
| 93-94 | Manufacturing Date | By Manufacturer | Variable | | | | | |
| 95-98 | Assembly Serial Number | By Manufacturer | Variable | | | | | |
| 99-127 | Manufacturer Specific Data | - | - | | | | | |
| 128~255 | Unused Storage Locations | Undefined | - | | | | | |